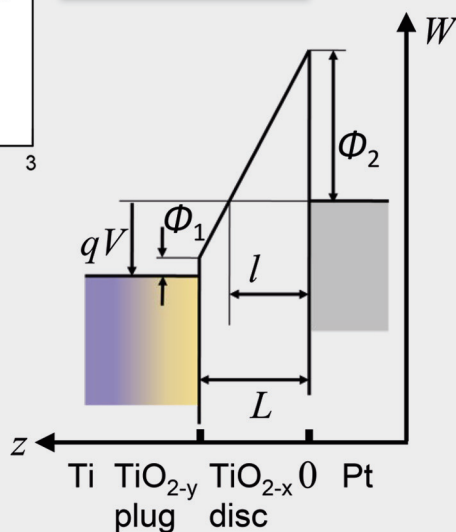
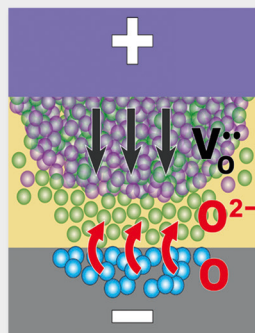
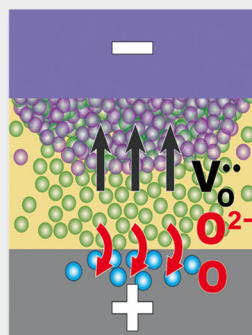
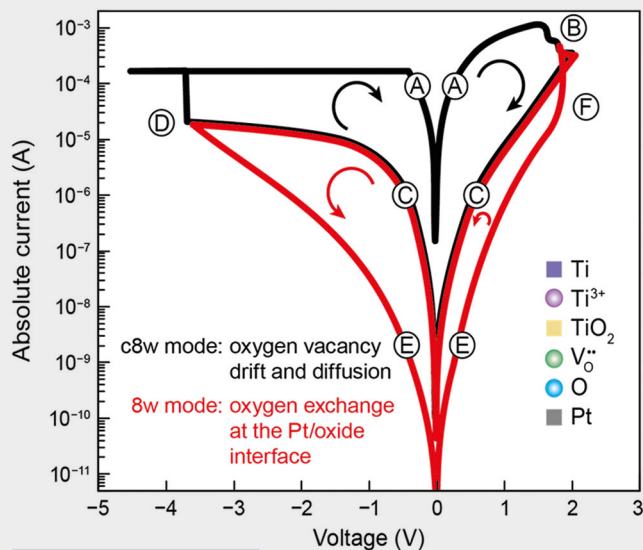




## Resistive switching phenomena in stacks of binary transition metal oxides grown by atomic layer deposition

Hehe Zhang

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